

Date	User	Material	Recipe	Substrate T	Thickness	Dep.time	Dep.time	JAW EC-400 (Woolam Spec.)		Avg index@632.8 nm	Index+1 %	Index-1%	Dep.rate (nm/min)	Target	Target+1	Target -	HF etch rate wafer	Stress	LPD (light point defects)			Avg dep.rate	Avg+10 %	Avg-10%	Additional Notes	
								Thick.	0%					10%	(nm/min)	Compress sive	before dep.		after dep.							
1/1/2012	User	SiO2	SiO2_10	250 °C	(Å)	min/sec	sec	Index at 632.8nm	Index at 1550nm																	
01/06/14	Biljana	SiO2	SiO2_10	250	1013.74	2'56.6"	176.6	1.463	1.459	1.457	1.472	1.443	34.44	1000.00	1100.00	900.00		-401.73	284	1059	35.35	38.89	31.82	4" Si wafer		
01/23/14	Biljana	SiO2	SiO2_10	250	1069.74	2'56.6"	176.6	1.456	1.446	1.457	1.472	1.443	36.34	1000.00	1100.00	900.00	604.28	-375.92	159	290	35.35	38.89	31.82	4" Si wafer		
02/03/14	Biljana	SiO2	SiO2_10	250	1047.82	2'56.6"	176.6	1.456	1.451	1.457	1.472	1.443	35.60	1000.00	1100.00	900.00	604.71	-346.54	304	451	35.35	38.89	31.82	4" Si wafer		
02/18/14	Biljana	SiO2	SiO2_10	250	1031.00	2'56.6"	176.6	1.454	1.444	1.457	1.472	1.443	35.03	1000.00	1100.00	900.00	545.75	-397.61	48	274	35.35	38.89	31.82	4" Si wafer		

Avg. Thick.	1040.58	Avg Index	1.457	Avg Rate	35.35	Target Th	1000.00
Th+10%	1144.63	Index+1%	1.472	Avg +10%	38.89	Target+1	1100.00
Th-10%	936.52	Index-1%	1.443	Avg -10%	31.82	Target-10	900.00

